



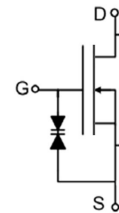
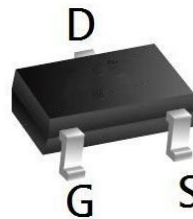
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

BVDSS	R _{DS(on)}	I _D
20V	17mΩ	6.0A

Description

The AO3416L is the high cell density trenched N-ch MOSFETs, which provides excellent R_{DS(on)} and efficiency for most of the small power switching and load switch applications. The AO3416L meet the RoHS and Green Product requirement with full function reliability approved. ESD Rating: 2000V HBM

SOT23 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±10	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 4.5V ¹	6.0	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 4.5V ¹	3.3	A
I _{DM}	Pulsed Drain Current ²	20.4	A
P _D @T _A =25°C	Total Power Dissipation ³	0.9	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	139	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	---	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}= \pm 10V$	-	-	± 10	μA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=4.5V, I_D=5A$	-	17	22	m Ω
		$V_{GS}=2.5V, I_D=3A$	-	26	36	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	545	-	pF
C_{oss}	Output Capacitance		-	103	-	pF
C_{rss}	Reverse Transfer Capacitance		-	90	-	pF
Q_g	Total Gate Charge	$V_{DS}=10V, I_D=5A,$ $V_{GS}=4.5V$	-	8	-	nC
Q_{gs}	Gate-Source Charge		-	2.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V, R_L=1.5\Omega,$ $R_{GEN}=3\Omega, V_{GS}=5V$	-	0.5	-	ns
t_r	Turn-on Rise Time		-	1	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	12	-	ns
t_f	Turn-off Fall Time		-	4	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=5A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

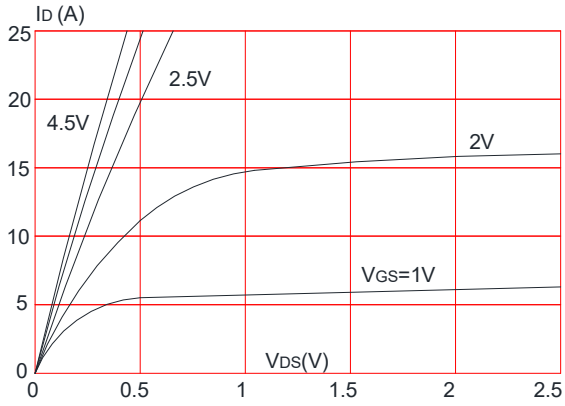


Figure 2: Typical Transfer Characteristics

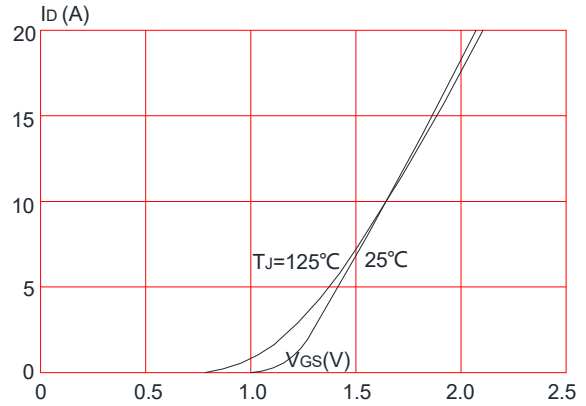


Figure 3: On-resistance vs. Drain Current

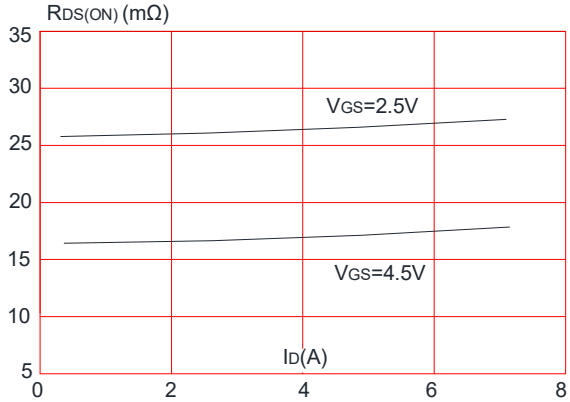


Figure 4: Body Diode Characteristics

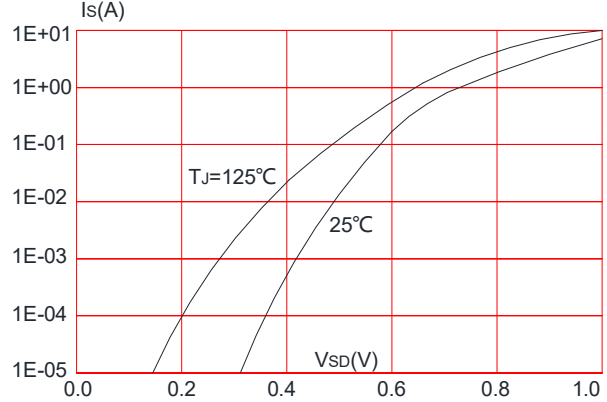


Figure 5: Gate Charge Characteristics

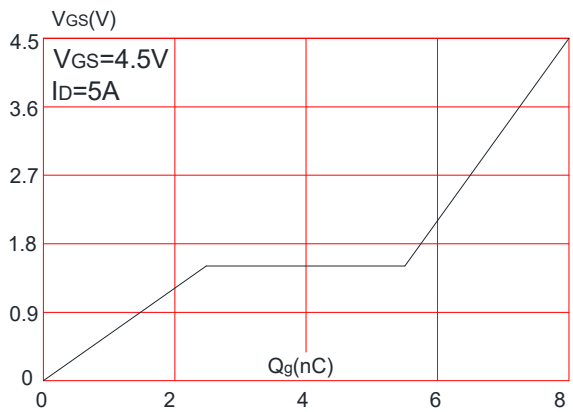


Figure 6: Capacitance Characteristics

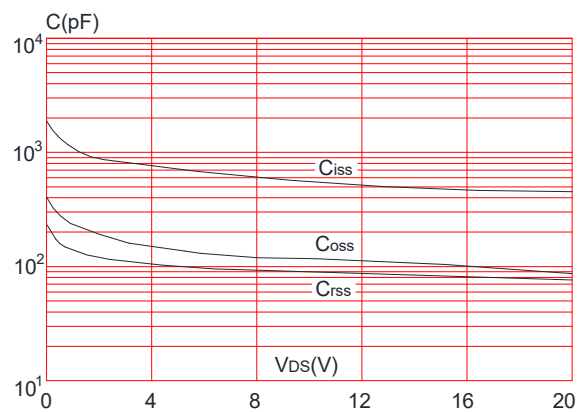
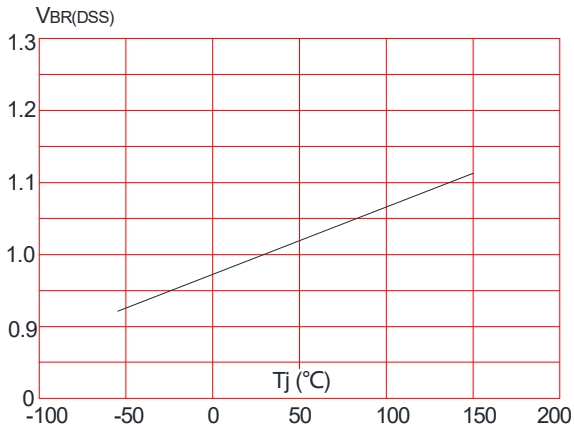
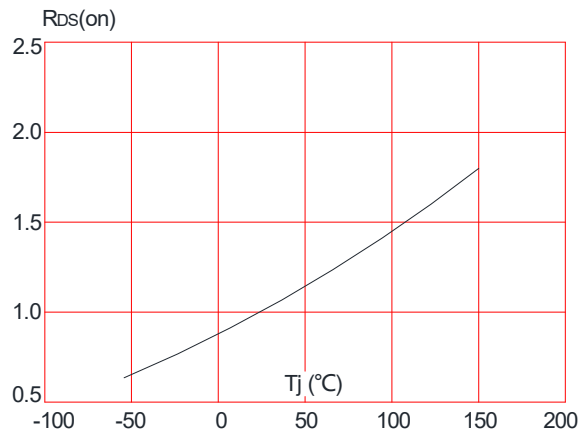
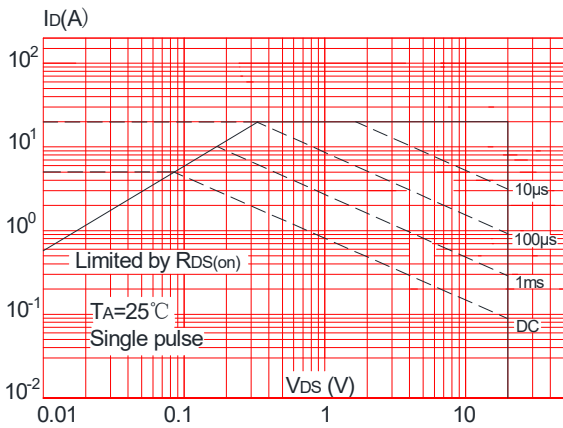
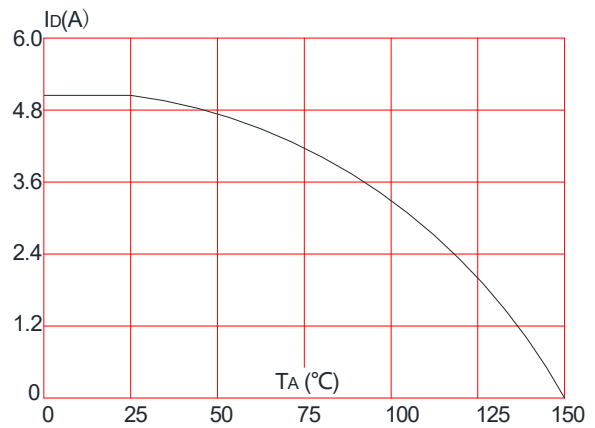
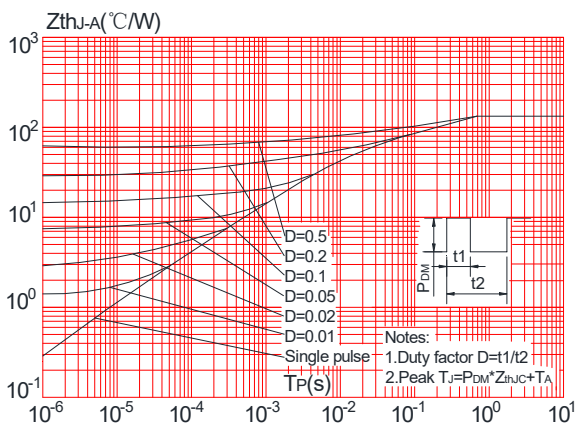
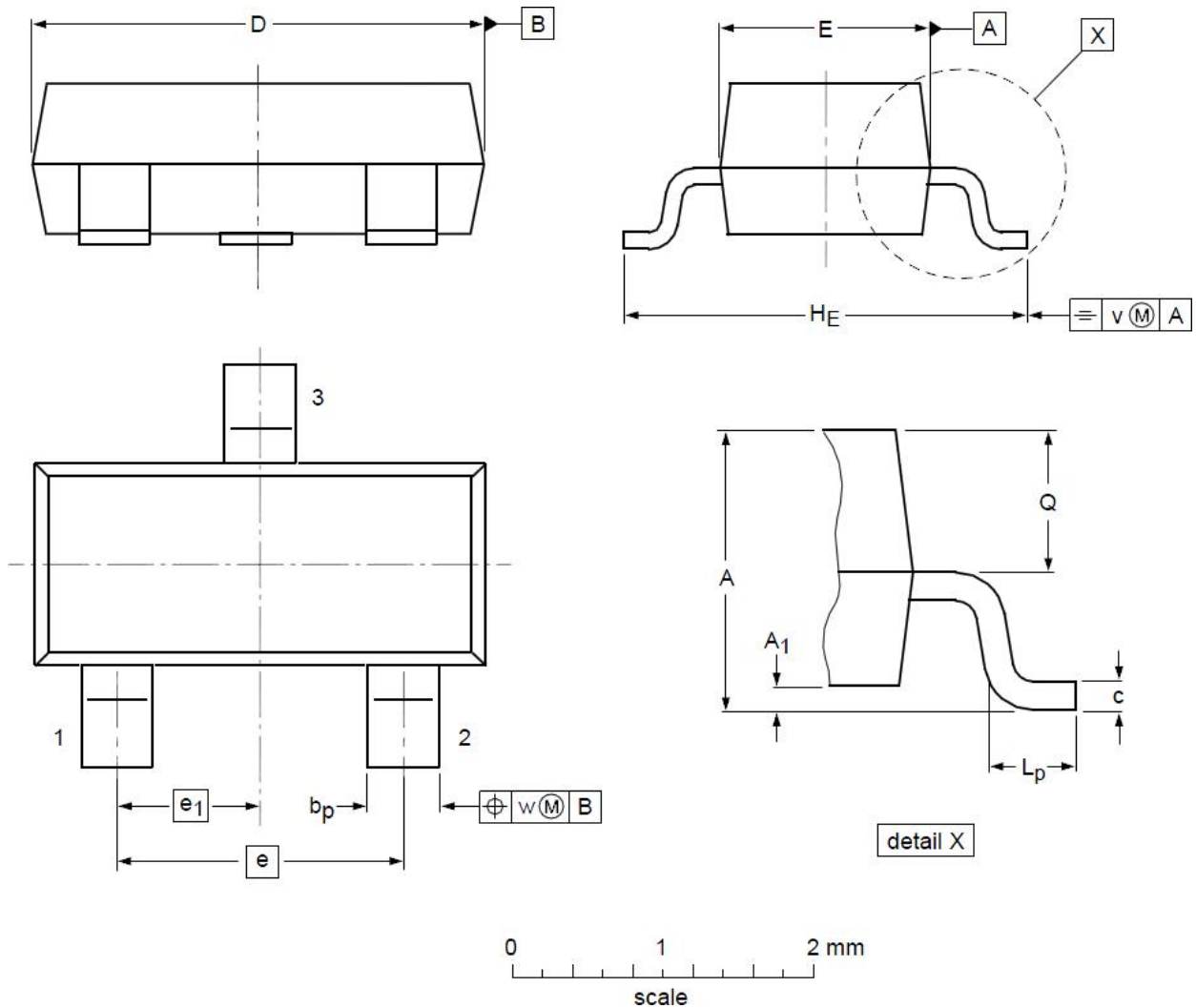


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Package Mechanical Data-SOT-23

DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				